

AMENDMENTS TO THE CLAIMS

This listing of claims replaces all prior listing of claims in this application.

Claims 1-25 (canceled).

26. (currently amended) A composition suitable for use in etching an insulative layer formed over a substrate in a semiconductor device, said composition ~~comprising~~ consisting of:

a flowing plasma etchant mixture consisting ~~essentially~~ of at least one fluorocarbon and ammonia, ~~wherein the a flow rate ratio of each fluorocarbon to ammonia is from about 2:1 to about 40:1.~~

27. (previously presented) The composition of claim 26, wherein said fluorocarbon is at least one member selected from the group consisting of fluorohydrocarbons, chlorofluorocarbons and chlorofluorohydrocarbons.

28. (original) The composition of claim 27, wherein said fluorocarbon is at least one member selected from the group consisting of C₄F₈, C₄F₆, C₅F₈, CF₄, C₂F₆, C₃F₈, CHF₃, and CH₂F₂.

29. (original) The composition of claim 26, wherein said fluorocarbon is at least one member selected from the group consisting of CF₄, CHF₃, and CH₂F₂.

30. (original) The composition of claim 29, wherein said fluorocarbon is at least two members selected from the group consisting of CF₄, CHF₃, and CH₂F₂.

31. (original) The composition of claim 30, wherein said fluorocarbon is a combination of CF₄, CHF₃, and CH₂F₂.

32. (previously presented) The composition of claim 26, wherein said composition is ineffective to remove side wall spacers of a gate stack formed over said substrate.

Claims 33-70 (canceled).

71. (currently amended) A composition suitable for use in etching an insulative layer formed on a substrate in a semiconductor device, said composition ~~comprising~~ consisting of:

a ~~flowing~~ plasma etchant mixture ~~comprising at least~~ consisting of at least two fluorocarbons CF_4 and NH_3 , ~~wherein the flow rate ratio of said CF_4 : NH_3 is greater than about 3:1.~~

Claims 72-76 (canceled).

77. (new) A composition suitable for use in etching an insulative layer formed over a substrate in a semiconductor device, said composition consisting of:

a gaseous etchant mixture consisting of at least one fluorocarbon and ammonia.